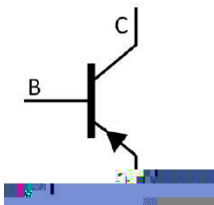
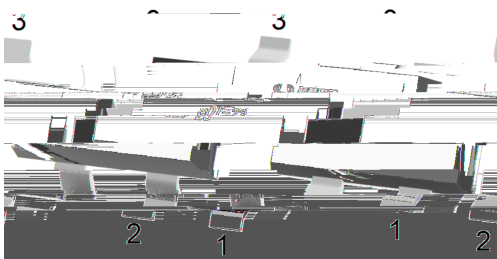


9 5 : .> // x 6 4 6 ! - } â 'ož Silicon PNP transistor in a SOT-23 Plastic Package.

(8 9 3 7 ; m k ... ` ' +) 7 ö Ö ä U ´ Å } L k —) í D } ož
Complementary pair with BRS8050MQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

9 ä y Ý è k á V ñ • } Lož
Power amplifier applications, Meet the stringent requirements of automotive applications.

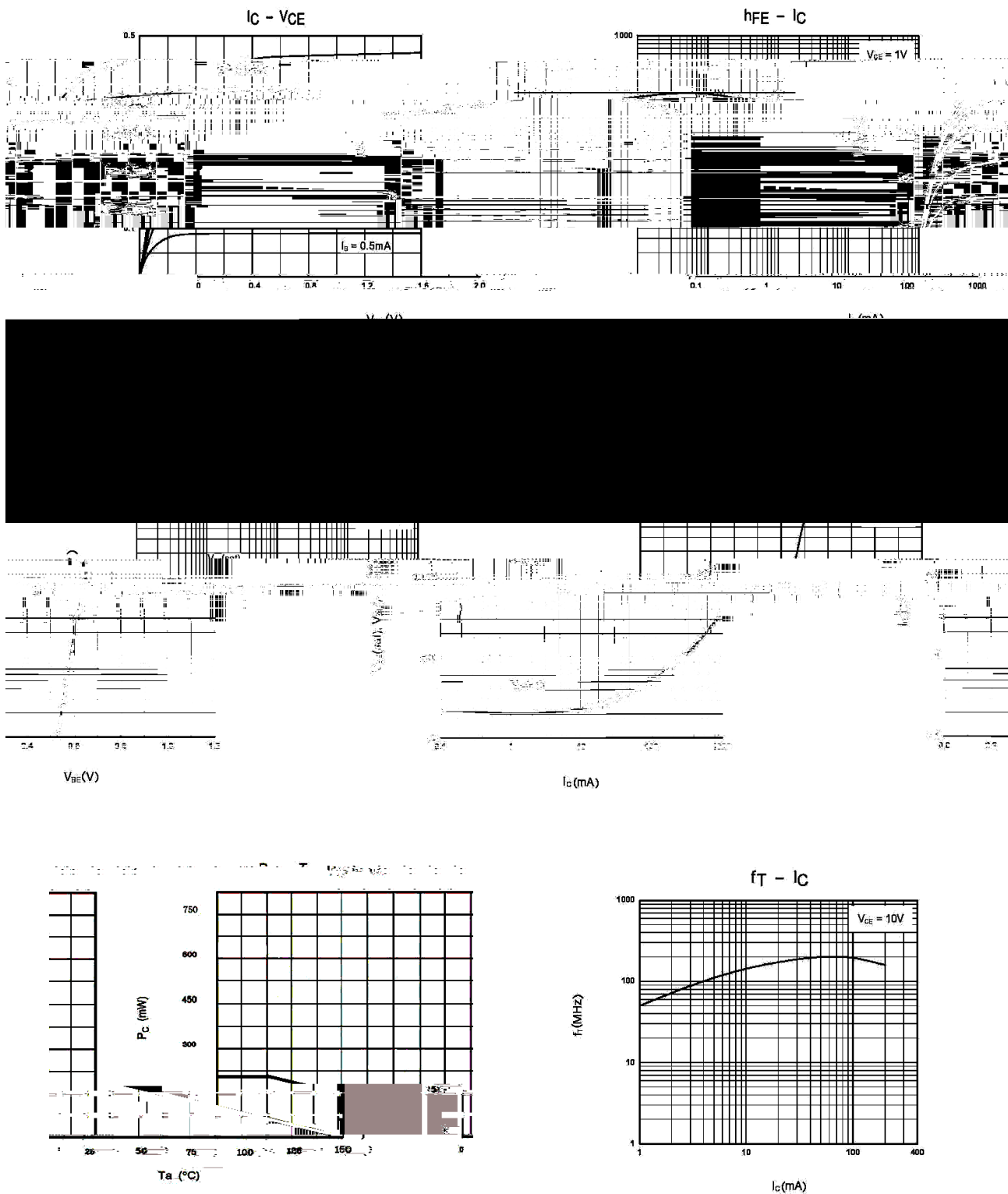


PIN1 y

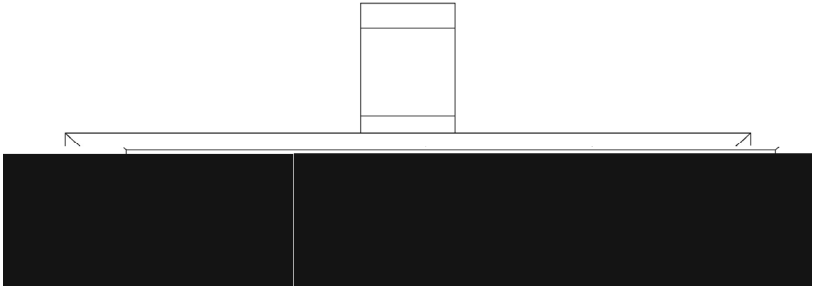
@ f Parameter	... Z Symbol	f > Rating	% y Unit
Collector to Base Voltage	V _{CBO}	-40	V
Collector to Emitter Voltage	V _{CEO}	-25	V
Emitter to Base Voltage	V _{EBO}	-6.0	V
Collector Current	I _C	-800	mA
Base Current	I _B	-200	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	
Storage Temperature Range	T _{stg}	-65 150	

@ f Parameter	... Z Symbol	y i Ú ^ Test Conditions	Â 4 > Min	Á ° > Typ	Â Ý > Max	% y Unit
Collector to Base Breakdown Voltage	V _{CBO}	I _C =-0.1mA I _E =0	-40			V
Collector to Emitter Breakdown Voltage	V _{CEO}	I _C =-2.0mA I _B =0	-25			V
Emitter to Base Breakdown Voltage	V _{EBO}	I _E =-0.1mA I _C =0	-6.0			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-35V I _E =0			-0.1	A
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-6.0V I _C =0			-0.1	A

Electrical Characteristic Curve



BRS8550MQ
Rev.C Mar.-2023



šWD t...•Ž¢ (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6

- ^a ¢ y

1o• Ä ½ “ † 150 ½200 - k ž • 60 ½120sec;

2o• Q › “ † 255 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.
- Note:

1.Preheating:150~200 - , Time:60~120sec.

2.Peak Temp.:255 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Resistance to Soldering Heat Test Conditions

“ † y 260 r5 - ž • y 10 r1 sec. Temp.:260±5 Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ~ E	Units/Reel / --	Units ;>û ¡H	Dimension ;>û p . (unit Åmm³)
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